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(54) Title: CONFORMAL THERMAL CVD WITH CONTROLLED FILM PROPERTIES AND HIGH DEPOSITION RATE

(57) Abstract: Methods and apparatuses for depositing dielectric films into features on semiconductor substrates are described herein. Methods involve depositing dielectric films by using controlled thermal chemical vapor deposition, with periodic passivation operations and densification to modulate film properties.

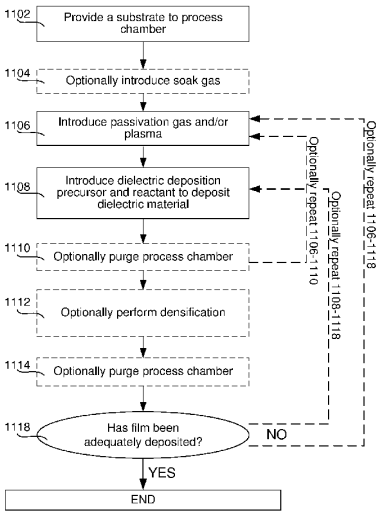


FIG. 11

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